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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/760,084	01/16/2004	Mikiko Abe	71801 CCD	1283

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c/o Cooper & Dunham LLP
1185 Ave. of the Americas
New York, NY 10036

EXAMINER

ANGEBRANNDT, MARTIN J

ART UNIT	PAPER NUMBER
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1795

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PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary	Application No. 10/760,084	Applicant(s) ABE ET AL.	
	Examiner Martin J. Angebrannt	Art Unit 1795	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 28 February 2008.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1,2,4-6 and 10-12 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1,2,4-6 and 10-12 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date <u>2/28/08</u> . | 6) <input type="checkbox"/> Other: _____ |

1. The response of the applicant has been read and given careful consideration. Rejections of the previous office action are withdrawn based upon the amendments and arguments of the applicant. Responses to the arguments of the applicant appear after the first rejection to which it is directed. The applicant has perfected priority through the certified translations provided.

2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 1,2,4-6 and 10-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Onaki et al. JP 2002-260283, in view of Ebina et al. JP 10-055539 and either (Nobukuni et al. '407 or Harigaya et al. EP 1260973).

Onaki et al. JP 2002-260283 (machine translation attached) teaches in example 2, a substrate with a 65 nm ZnS- Nb₂O₅ lower protective layer, a 5 nm second lower dielectric layer of (ZrO₂)₈₀ (Nb₂O₅)₂₀ , a 15 nm In₅Sb₆₂Te₃₀Ge₃ recording layer, a 16 nm dielectric layer of (ZrO₂)₈₀ (Nb₂O₅)₂₀ , a AgCu reflective layer of 150 nm. Examples 4 uses ZrO₂-MgO [0087], example 5 uses ZrO₂-CaO [0090]. The use of a bilayer lower dielectric protective layer, where the layer closest to the recording layer acts as a barrier layer and zirconia materials are preferred [0041,0047-0048]. Another example uses ZrO₂-Y₂O₃-TiO₂ [0093]. The use of zirconia stabilized using various materials is disclosed. [0019,0068].

Ebina et al. JP 10-055539 in example 1 teaches a grooved substrate coated with a 150 nm ZnS-SiO₂ lower protective layer, a 25 nm Sb₂Te₃Ge₂ recording layer, a 50 nm ZnS-SiO₂ upper protective layer, a 100 nm Al reflective layer [0016]. This was initialized with a power density

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of $17.5 \text{ mW}/\mu\text{m}^2$ at a linear velocity of 8.0 m/s with an advance of 48 microns. [0017]. . The laser beams used was a 100×1 micron oval laser beam (area being $78.5 \mu\text{m}^2$ [0017]. The use of the medium at velocities of 8.4 m/s is disclosed. [0017]. The use of velocities of 3-12 m/s is disclosed/ [0009]. The use of power densities of $7.5\text{-}20 \text{ mW}/\mu\text{m}^2$ is disclosed [0010]. The use of various phase change recording layers including InSbTe and GeTeSb recording layers is disclosed [0014]. The power of the laser is varied inversely with speed.

Nobukuni et al. '407 teaches example 1, which has a InGeSbTe recording layer and is initialized at 3-4 m/s and a power of 600-700 mW over an area of $71.4 \mu\text{m}^2$. The power is $\sim 9.8 \text{ mW}/\mu\text{m}^2$. [0549]. The use of the medium at 10 times velocity is taught ($\sim 12.0 \text{ m/s}$). [0556-0572]. The general use of GeTeSb and InGeSbTe recording layers is disclosed [0160,0166,0179]. Example 11 teaches the initialization of the media at 2, 2.5, 3, 7 and 10 m/s at powers of 500 to 1500 mW with a laser beam which has an area of 102.05 sq. microns. The power/area is $14.69 \text{ mW}/\text{sq. micron}$.

Harigaya et al. EP 1260973 in example 1 teaches a substrate with a 0.74 micron pitch groove coated with a 68 nm ZnS-SiO₂ lower protective layer, a 16 nm GeMnSbTe recording layer, a 10 nm 77% ZrO₂-3% Y₂O₃-20% TiO₂ upper interfacial layer and a 140 nm Ag reflective layer. [0142-0149]. This was initialized with a laser power of 850 mW at a linear velocity of 3 m/s and a feed of 36 microns/r [0152]. The laser beams used was a 196×1 micron oval laser beam and each area was irradiated and average of 5.4 times (area being $153 \mu\text{m}^2$) [0152]. The use of the medium at 17.5 m/s is disclosed [0152].

It would have been obvious to one skilled in the art to modify example 2 of Onaki et al. JP 2002-260283 by using CaO, MgO and or ReO based upon the direction at

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[0019,0068,0078,0090] and using the initialization process of Ebina et al. JP 10-055539 with a reasonable expectation of being able to initialize the media at velocities of 8-12 m/s at power densities of 15-20 mW/ μm^2 based upon the similarity with the media of Nobukuni et al. '407 or Harigaya et al. EP 1260973 which are disclosed as functioning at higher velocities as well. Further it would have been obvious to modify the process by using CaO, MgO and or ReO in combination with ZrO_2 and up to 20% TiO_2 based upon the direction at [0019]. Note that Ebina et al. JP 10-055539 teaches the recording media can be used at velocities of 3-12 m/s with embraces the value taught for Onaki et al. JP 2002-260283.

The addition of Onaki et al. JP 2002-260283 addresses the arguments by the applicant based upon ZrO_2 dielectric layers.

The claims require the following structure, a substrate, a first/lower protective layer, a recording layer, a second/upper protective layer and a reflective layer, with a ZrO_2 oxide layer between the recording layer and either or both of the protective layers. As the layer 5 nm thick $(\text{ZrO}_2)_{80}(\text{Nb}_2\text{O}_5)_{20}$ layer of Onaki et al. JP 2002-260283 is between the recording layer and the $\text{ZnS}-\text{Nb}_2\text{O}_5$ lower protective layer, the layer structure is met by the cited example 2 and with the substitution rendered obvious by the teachings at [0019,0068,0078,0090] of Onaki et al. JP 2002-260283, the composition and layered structure is taught. To argue that the $(\text{ZrO}_2)_{80}(\text{Nb}_2\text{O}_5)_{20}$ layer is not an oxide layer as on page 8 of the response is entirely without merit (O is the atomic symbol for oxygen). The claims do not require the oxide layer on both sides of the recording layer, so the upper protective layer composition is moot. The basis for the ratios being maintained is that of disclosed equivalence, such as at [0019,0068,0078,0090] of Onaki et al. JP 2002-260283. It would be ridiculous to assert or assume changes in the ratios without a specific

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teaching to that effect. The use of higher linear velocities is taught by Ebina et al. JP 10-055539 and Nobukuni et al. '407 and has the simple advantage of being able to initialize the media in less time than slower velocities and the ranges taught by Ebina et al. JP 10-055539 and Nobukuni et al. '407 provide a reasonable expectation of success, noting that these teachings are within the phase change optical recording media arts and therefore analogous. Ebina et al. JP 10-055539 teaches the velocities of 3-12 m/s [0009] as well as the use of power densities of 7.5-20 mW/ μm^2 [0010] and so these features are taught, contrary to the position of the applicant on pages 10 and 11. The rejection stands.

The applicant's arguments fails to account for the open 'comprising' language used in the claims, which embraced the addition of other, unspecified layers. The applicants examples include other protective layers beyond the recited stabilized zirconia layer as evidenced by the example 1 [0139-0145] and figures 5-9. The thermal properties are affected by all the layers. **The applicant's data in figure 2 is interesting as it shows a minima for jitter as a function of power density (noting that figure 3 does not). As the exposure is a function of the power density and the exposure duration, and the discussion of this figure in the specification (nor the claims) does not describe the other conditions, such as linear velocity and number of passes across the same spot. The applicant may wish to provide similar data for the various velocities in declaration form which show minima. The applicant may have this data on hand and merely need to reorder it. Such a showing together with limiting the claims to preclude multiple irradiation in the independent claims (it appears in claim 12) could render the resultant claims patentable.**

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4. Claims 1,2,4-6, and 10-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Onaki et al. JP 2002-260283, in view of Ebina et al. JP 10-055539 (machine translation enclosed), combined with (Nobukuni et al. '407 or Harigaya et al. EP 1260973), further in view of Maeda et al. '375.

Maeda et al. '375 disclose the initialization of phase change recording media in only the groove or land areas.

In addition to the basis above, to address the embodiments bounded by the claims where multiple irradiation does not occur, the examiner holds that it would have been obvious to one skilled in the art to modify the processes rendered obvious by the combination of Onaki et al. JP 2002-260283, Ebina et al. JP 10-055539, Nobukuni et al. '407 or Harigaya et al. EP 1260973 by initializing only the land or groove regions as taught by Maeda et al. '375 to reduce the time required for initialization.

The examiner does not assert that Maeda et al. '375 teaches the irradiation conditions, but teaches the irradiation of only the portions of the recording layer which are to be used, specifically the land or the groove areas, rather than initializing the entire media, only approximately $\frac{1}{2}$ of the recording layer would be initialized, so this represents a clear time savings of approximately $\frac{1}{2}$ the initialization time required to initialize the entire medium surface. The rejection stands.

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Martin J. Angebrannndt whose telephone number is 571-272-1378. The examiner can normally be reached on Monday-Friday.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark Huff can be reached on 571-272-1385. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Martin J Angebranndt/
Primary Examiner, Art Unit 1795

Martin J Angebranndt
Primary Examiner
Art Unit 1795

5/8/2008